

PHOTOMASK AND ITS PRODUCTION

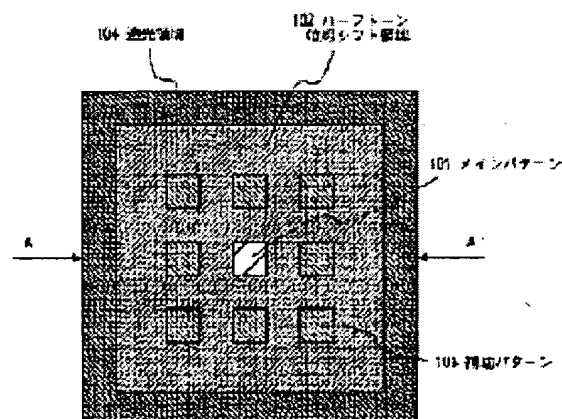
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 - International: **G03F1/00; G03F1/14; G03F1/00; G03F1/14; (IPC1-7): G03F1/08; H01L21/027**
 - european: **G03F1/00G6; G03F1/14G**
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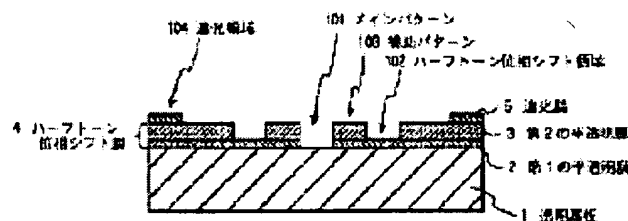
Abstract of JP11143047

PROBLEM TO BE SOLVED: To provide a photomask capable of improving the focusing characteristic of a translucent auxiliary pattern mask by a halftone phase shift photomask and a process for producing the same. **SOLUTION:** The halftone phase shift mask arranged with the translucent auxiliary patterns 103 on the peripheries of a main pattern 101 is produced. The halftone phase shift photomask is so set that a prescribed phase error (a deviation from 180 deg. of a phase difference) occurs in the transmitted light of this photomask, by which the inclination of the focusing characteristic of the main pattern 101 by the translucent auxiliary patterns 103 is corrected.

(a)



(b)



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